

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of  
Shunpei YAMAZAKI et al.

Serial No. 09/932,935

Filed: August 21, 2001

For: LASER APPARATUS, LASER )

ANNEALING METHOD, AND )

MANUFACTURING METHOD OF A )

SEMICONDUCTOR DEVICE )

Art Unit: 2812

Examiner: V. Simkovic



CERTIFICATE OF MAILING

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*Adele M. Stamper*  
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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The present application is the parent of U.S. Patent Application Publication No. 2002/0048864.


As a supplement to the Information Disclosure Statement filed January 25, 2002, the Applicants submit the cover page of Helen et al., "Reproducible High Field Effect Mobility Polysilicon Thin Film Transistors Involved Pulsed Nd:YVO<sub>4</sub> Laser Crystallization," pp. 297-300, 1999, IEDM 0-7803-5410-9/99 IEEE, which shows that the publication of the Helen reference was December 5-8, 1999.

This Information Disclosure Statement is being submitted with an RCE. Therefore, no fee is required.

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The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be required now or hereafter, or credit any overpayment to Deposit Account No. 50-2280. A duplicate copy of this sheet is attached.

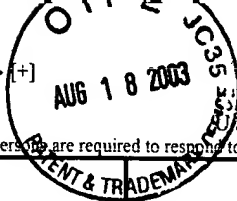
Respectfully submitted,



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Substitute for form 1449A/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				Application Number	09/932,935
				Filing Date	August 21, 2001
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2812
				Examiner Name	V. Simkovic
Sheet	1	of	1	Attorney Docket Number	0756-2351

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> <i>(if known)</i>			
		2002/0048864		Yamazaki et al.	04/25/2002	

FOREIGN PATENT DOCUMENTS								
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> <i>(if known)</i>				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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		Cover page of Helen et al., "Reproducible High Field Effect Mobility Polysilicon Thin Film Transistors Involved Pulsed Nd:YVO <sub>4</sub> Laser Crystallization," pp. 297-300, IEDM 7803-5410-9/99 IEEE, December 5-8, 1999.	

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<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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